**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- · Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V	
V <sub>GS</sub>	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	220	mA	
Static characteristics								
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	2.2	3	Ω	

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D1 D2
2	G1	gate 1	654	
3	D2	drain 2		G1 A A A BLANCE
4	S2	source 2	0	\
5	G2	gate 2	1 2 3	
6	D1	drain 1	TSSOP6 (SOT363)	S1 S2 017aaa256

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BSS138AKS-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

## 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
BSS138AKS-Q	J4%

[1] % = placeholder for manufacturing site code

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or			'		
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	220	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	160	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.8	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	270	mW
			[1]	-	310	mW
		T <sub>sp</sub> = 25 °C		-	1.3	W
Per device	-			,		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	405	mW
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source Drai	n Diode (per transistor)					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	210	mA
ESD maxim	um rating (per transistor)					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		-	500	V
Avalanche r	uggedness (per transistor)					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 20 mA; DUT in avalanche (unclamped)		-	6.6	mJ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### 60 V, dual N-channel Trench MOSFET

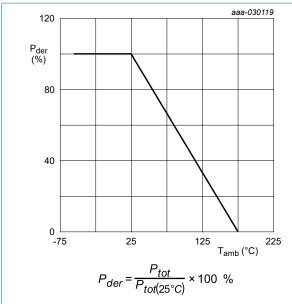


Fig. 1. Normalized total power dissipation as a function of ambient temperature

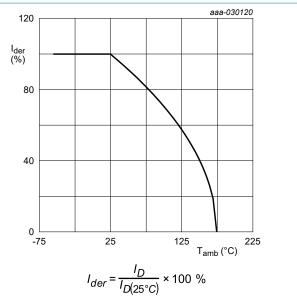


Fig. 2. Normalized continuous drain current as a function of ambient temperature

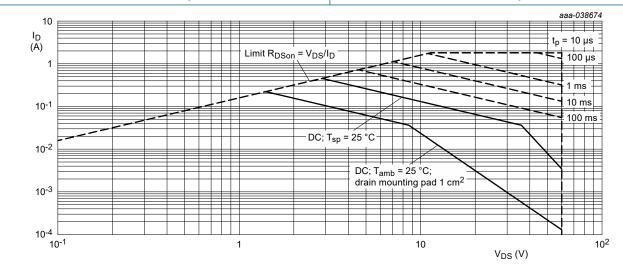


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device	<u>'</u>					'	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	375	K/W
Per transisto	or						
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	500	560	K/W
	junction to ambient		[2]	-	450	480	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	80	115	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

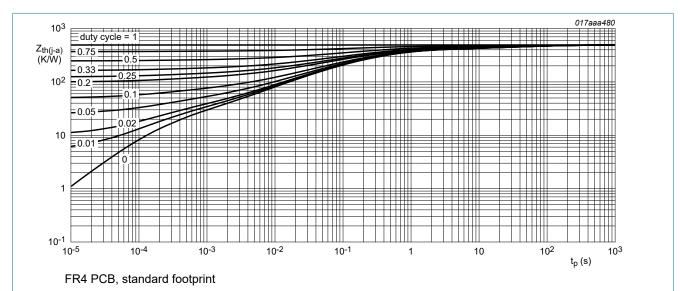


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

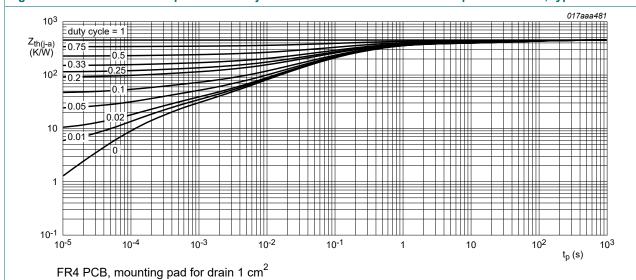


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.8	1.1	1.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	500	nA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	5	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	500	nA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-500	nA
Doon	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	2.2	3	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 175 °C	-	4.6	6.3	Ω
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 50 mA; T <sub>j</sub> = 25 °C	-	2.7	3.9	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 10 mA; T <sub>j</sub> = 25 °C	-	3.4	12	Ω
g <sub>fs</sub>	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	0.3	-	S
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 100 mA; V <sub>GS</sub> = 10 V;	-	0.21	0.315	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.022	-	nC
$Q_{GD}$	gate-drain charge	1	-	0.051	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	9	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	1.8	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.1	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 100 mA; V <sub>GS</sub> = 10 V;	-	1	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	1	-	ns
d(off)	turn-off delay time	1	-	2	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-dra	in diode				1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 210 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	1	1.7	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 210 mA; dI <sub>S</sub> /dt = -100 A/µs;	-	7	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V; T <sub>i</sub> = 25 °C	_	1		nC

### 60 V, dual N-channel Trench MOSFET

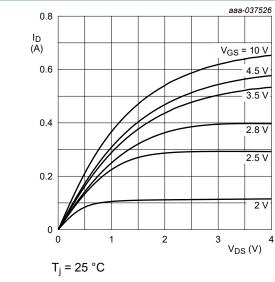


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

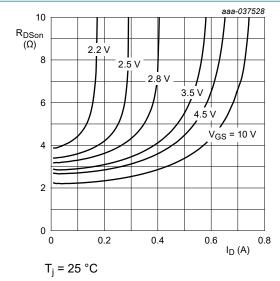
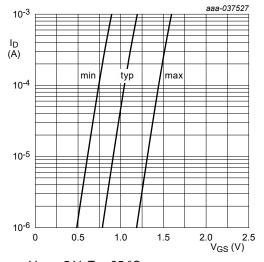


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $V_{DS} = 5 \text{ V}; T_j = 25 ^{\circ}\text{C}$ 

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

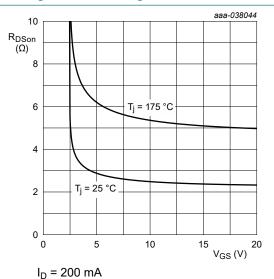


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, dual N-channel Trench MOSFET

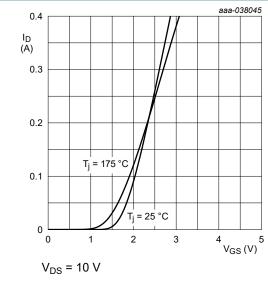


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

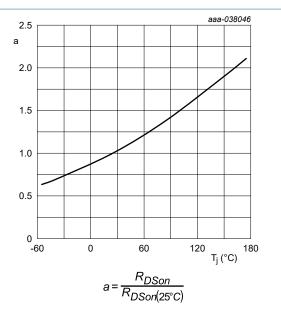


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

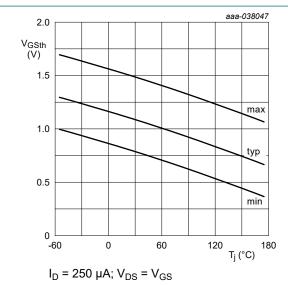


Fig. 12. Gate-source threshold voltage as a function of junction temperature

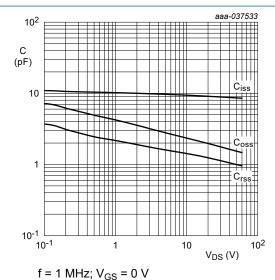


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

## 60 V, dual N-channel Trench MOSFET

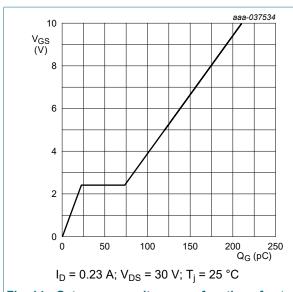


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

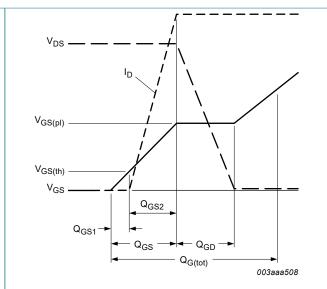


Fig. 15. Gate charge waveform definitions

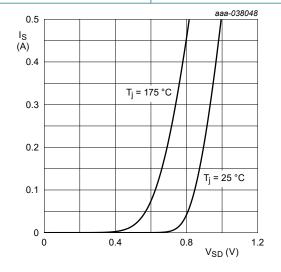
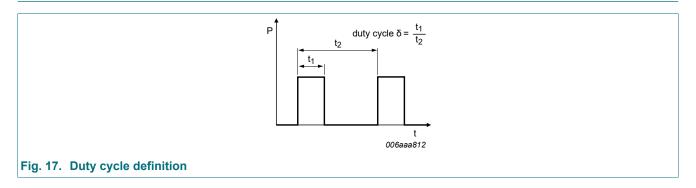


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline

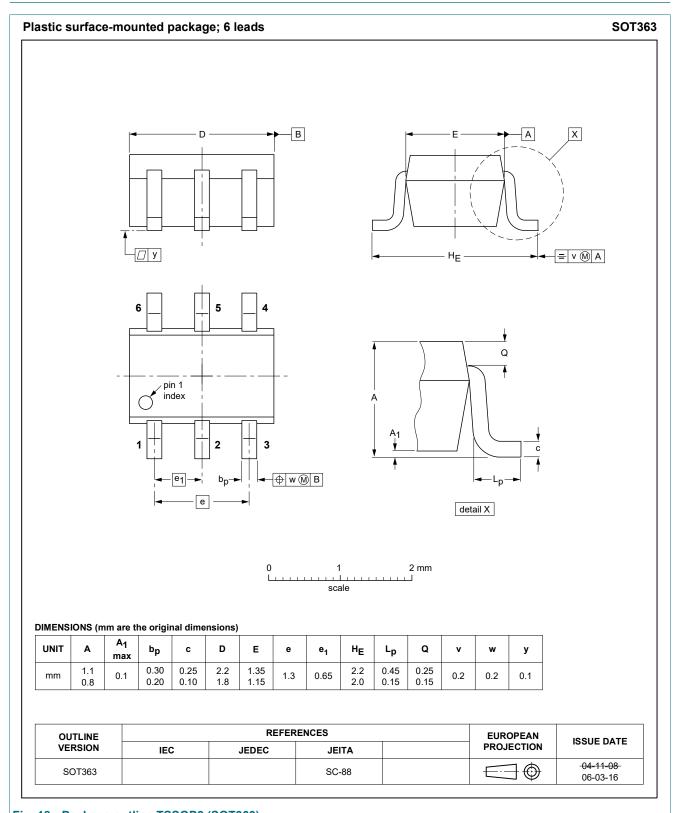
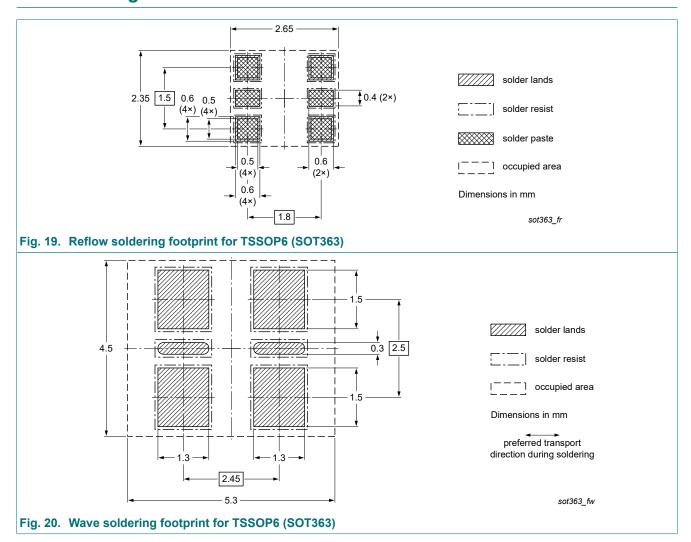


Fig. 18. Package outline TSSOP6 (SOT363)

## 60 V, dual N-channel Trench MOSFET

## 13. Soldering



60 V, dual N-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS138AKS-Q v.1	20240216	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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